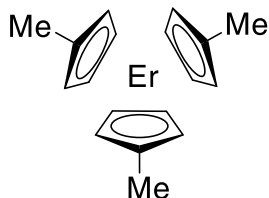


Catalog # 68-8740 Tris(methylcyclopentadienyl)erbium(III) (99.9%-Er) (REO)



Thermal Behavior:

- Melting point: 135°C [1]
- TGA data and diagram is available in [1]

Technical Notes:

1. Precursor used for erbium thin film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
Er ₂ O ₃	ALD	-	0.3 Torr	O ₂ /O ₃	200-375°C	1
	ALD	95°C	0.5 Torr	O ₃	170-330°C	2
	ALD	115°C	1.5-2.25 Torr	H ₂ O	175-450°C	3
	ALD	170°C	-	H ₂ O	300°C	4
Er _x Ti _{1-x} O _y	ALD	100°C	-	TDEAT, O ₃	175-250°C	5
Er _x Y _y O _z	ALD	115°C	1.5-2.25 Torr	Cp ₃ Y, H ₂ O	RT	6
Er _x Ga _{2-x} O ₃	ALD	112°C	1.5-2.25 Torr	(NM ₂) ₆ Ga, H ₂ O	250-350°C	7

References:

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4. [Mater. Lett. 2020, 263, 127216.](#)
5. [ECS J. Solid State Sci. Technol. 2012, 1, N107.](#)
6. [Appl. Phys. Lett. 2013, 103, 193109.](#)
7. [J. Mater. Chem., 2007, 17, 1308.](#)